

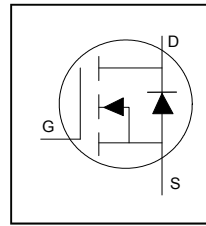
### Application

- Brushed Motor drive applications
- BLDC Motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- OR-ing and redundant power switches
- DC/DC and AC/DC converters
- DC/AC Inverters

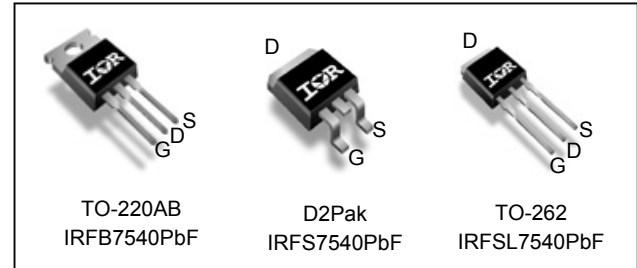
### Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free, RoHS Compliant

HEXFET® Power MOSFET

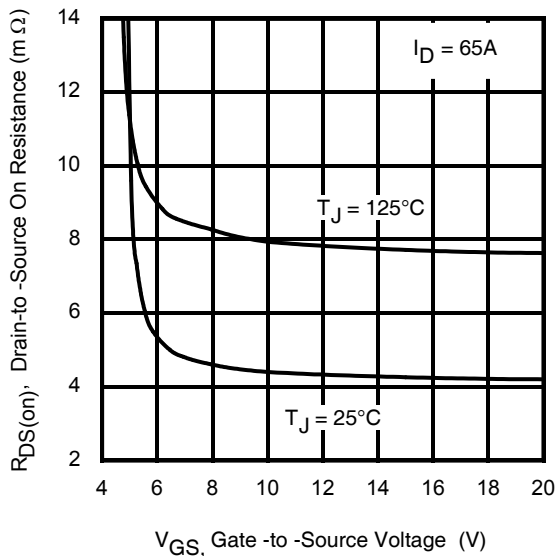


|                                |              |
|--------------------------------|--------------|
| <b>V<sub>DSS</sub></b>         | <b>60V</b>   |
| <b>R<sub>DS(on)</sub> typ.</b> | <b>4.2mΩ</b> |
|                                | <b>5.1mΩ</b> |
| <b>I<sub>D</sub></b>           | <b>110A</b>  |

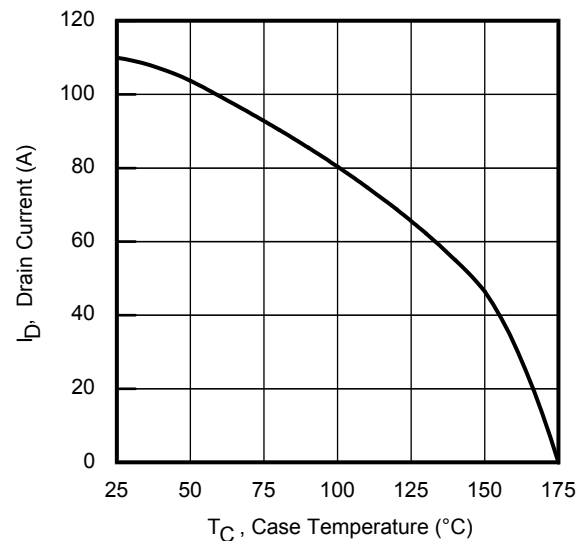


|          |          |          |
|----------|----------|----------|
| <b>G</b> | <b>D</b> | <b>S</b> |
| Gate     | Drain    | Source   |

| Base part number | Package Type | Standard Pack      |          | Orderable Part Number |
|------------------|--------------|--------------------|----------|-----------------------|
|                  |              | Form               | Quantity |                       |
| IRFB7540PbF      | TO-220       | Tube               | 50       | IRFB7540PbF           |
| IRFSL7540PbF     | TO-262       | Tube               | 50       | IRFSL7540PbF          |
| IRFS7540PbF      | D2-Pak       | Tube               | 50       | IRFS7540PbF           |
|                  |              | Tape and Reel Left | 800      | IRFS7540TRLpBF        |



**Fig 1.** Typical On-Resistance vs. Gate Voltage



**Fig 2.** Maximum Drain Current vs. Case Temperature

**Absolute Maximum Rating**

| Symbol                          | Parameter   | Max.                | Units |
|---------------------------------|---|---------------------|-------|
| $I_D @ T_C = 25^\circ\text{C}$  | Continuous Drain Current, $V_{GS} @ 10\text{V}$         | 110                 | A     |
| $I_D @ T_C = 100^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$         | 80                  |       |
| $I_{DM}$                        | Pulsed Drain Current ①                                  | 430                 |       |
| $P_D @ T_C = 25^\circ\text{C}$  | Maximum Power Dissipation                               | 160                 | W     |
|                                 | Linear Derating Factor                                  | 1.1                 | W/°C  |
| $V_{GS}$                        | Gate-to-Source Voltage                                  | $\pm 20$            | V     |
| $T_J$<br>$T_{STG}$              | Operating Junction and Storage Temperature Range        | -55 to + 175        | °C    |
|                                 | Soldering Temperature, for 10 seconds (1.6mm from case) | 300                 |       |
|                                 | Mounting Torque, 6-32 or M3 Screw                       | 10 lbf-in (1.1 N·m) |       |

**Avalanche Characteristics**

|                              |                                 |                          |    |
|------------------------------|---------------------------------|--------------------------|----|
| $E_{AS}$ (Thermally limited) | Single Pulse Avalanche Energy ② | 180                      | mJ |
| $E_{AS}$ (Thermally limited) | Single Pulse Avalanche Energy ③ | 313                      |    |
| $I_{AR}$                     | Avalanche Current ①             | See Fig 15, 16, 23a, 23b | A  |
| $E_{AR}$                     | Repetitive Avalanche Energy ①   |                          | mJ |

**Thermal Resistance**

| Symbol          | Parameter  | Typ. | Max. | Units |
|-----------------|--|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ⑦                                     | —    | 0.95 | °C/W  |
| $R_{\theta CS}$ | Case-to-Sink, Flat Greased Surface (TO-220)            | 0.50 | —    |       |
| $R_{\theta JA}$ | Junction-to-Ambient (TO-220)                           | —    | 62   |       |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount) (D <sup>2</sup> Pak) ⑧ | —    | 40   |       |

**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

| Symbol                          | Parameter                            | Min. | Typ. | Max. | Units | Conditions   |
|---------------------------------|--------------------------------------|------|------|------|-------|--|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 60   | —    | —    | V     | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$                         |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 48   | —    | mV/°C | Reference to 25°C, $I_D = 1\text{mA}$                              |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | 4.2  | 5.1  | mΩ    | $V_{GS} = 10\text{V}, I_D = 65\text{A}$                            |
|                                 |                                      | —    | 5.4  | —    |       | $V_{GS} = 6.0\text{V}, I_D = 33\text{A}$                           |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.1  | —    | 3.7  | V     | $V_{DS} = V_{GS}, I_D = 100\mu\text{A}$                            |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —    | 1.0  | μA    | $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$                          |
|                                 |                                      | —    | —    | 150  |       | $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$ |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 100  | nA    | $V_{GS} = 20\text{V}$  |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -100 |       | $V_{GS} = -20\text{V}$   |
| $R_G$                           | Gate Resistance                      | —    | 2.2  | —    | Ω     |  |

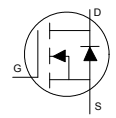
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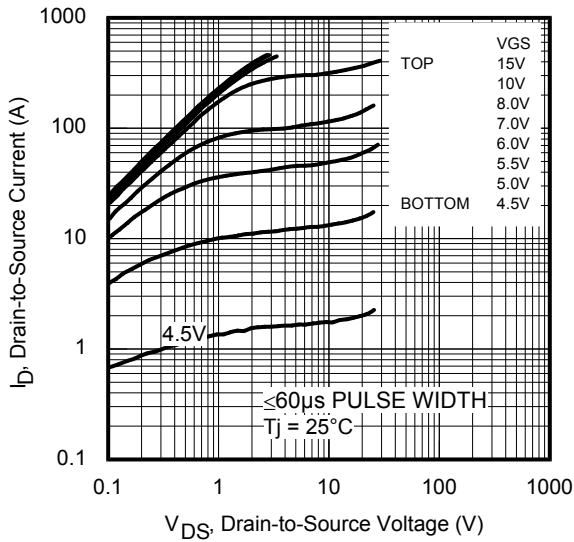
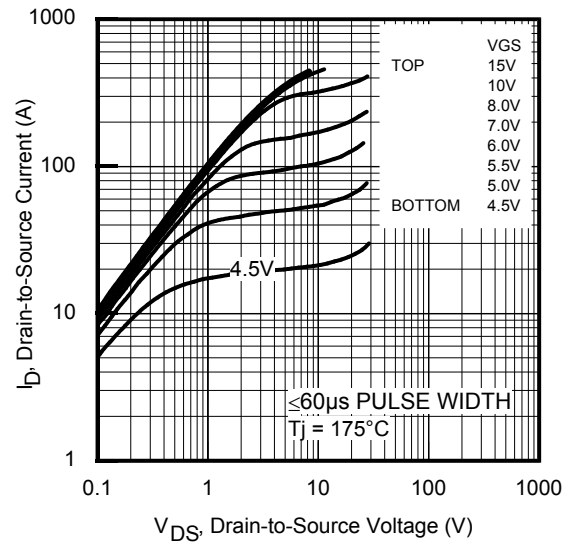
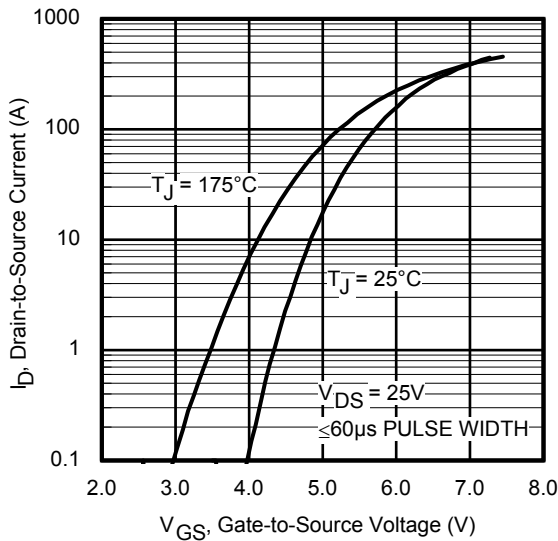
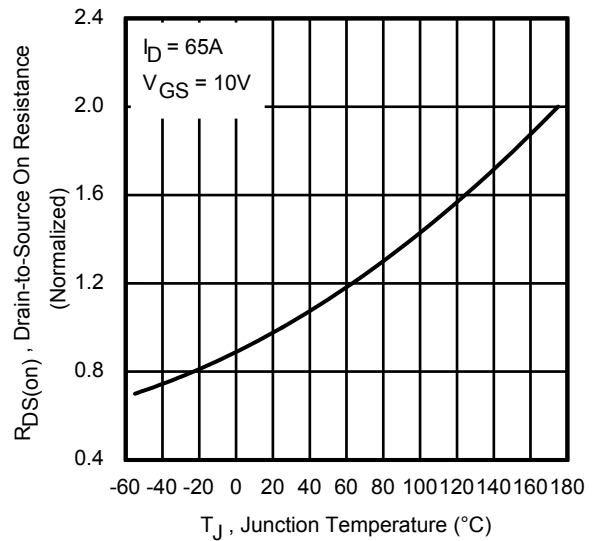
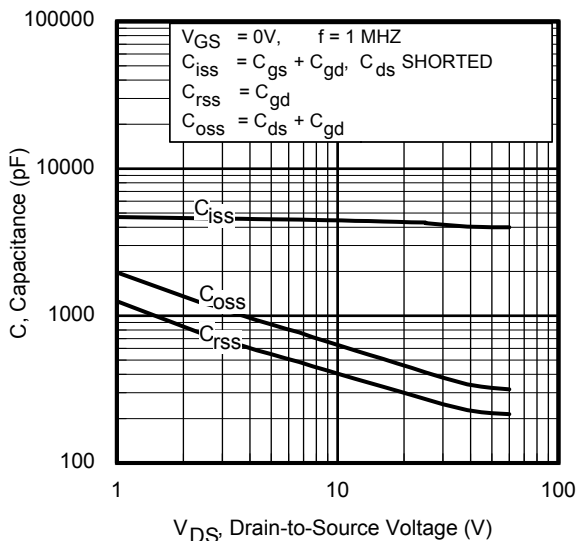
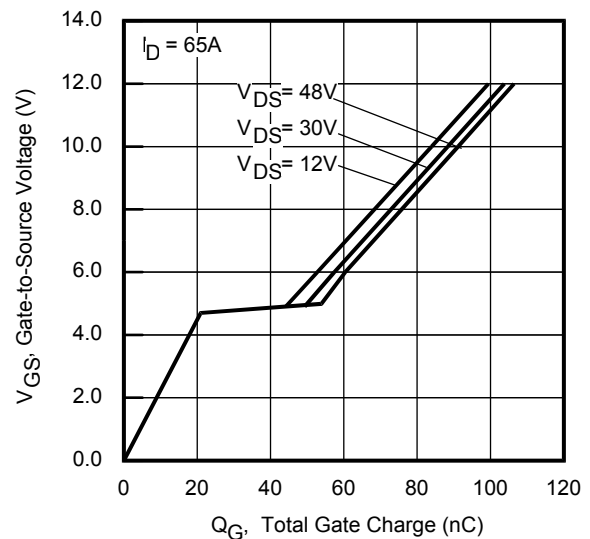
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 86\mu\text{H}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 65\text{A}$ ,  $V_{GS} = 10\text{V}$ .
- ③  $I_{SD} \leq 65\text{A}$ ,  $di/dt \leq 1130\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. (TR) is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $C_{oss}$  eff. (ER) is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦  $R_\theta$  is measured at  $T_J$  approximately 90°C.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994: <http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑨ Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 1\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 25\text{A}$ ,  $V_{GS} = 10\text{V}$ .

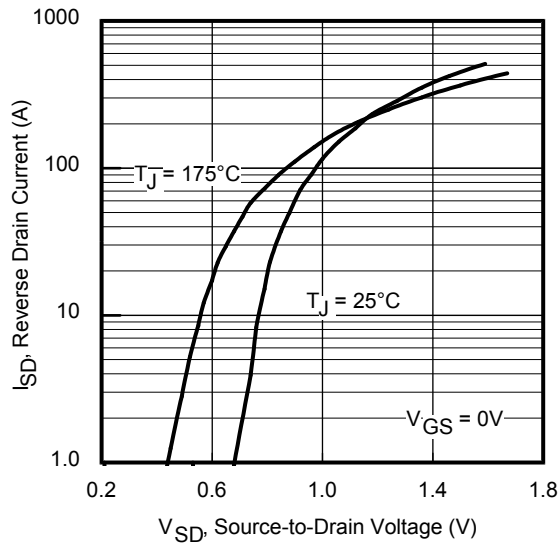
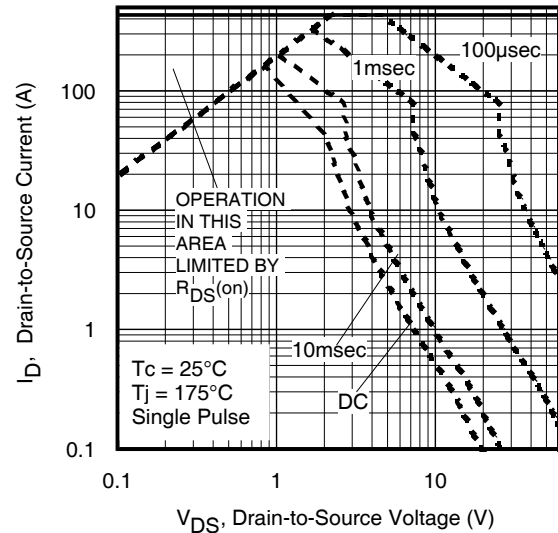
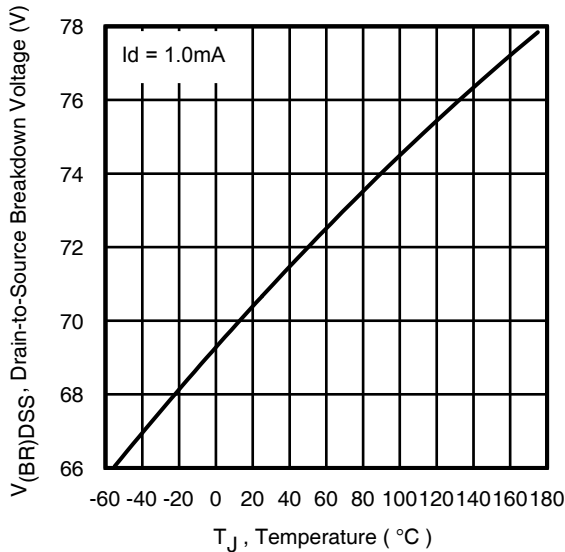
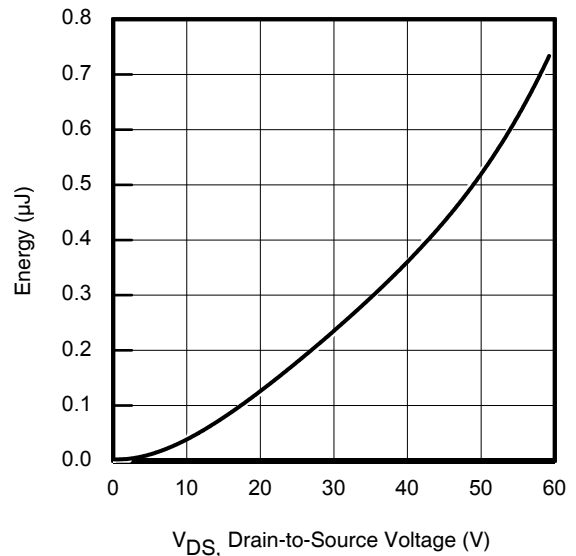
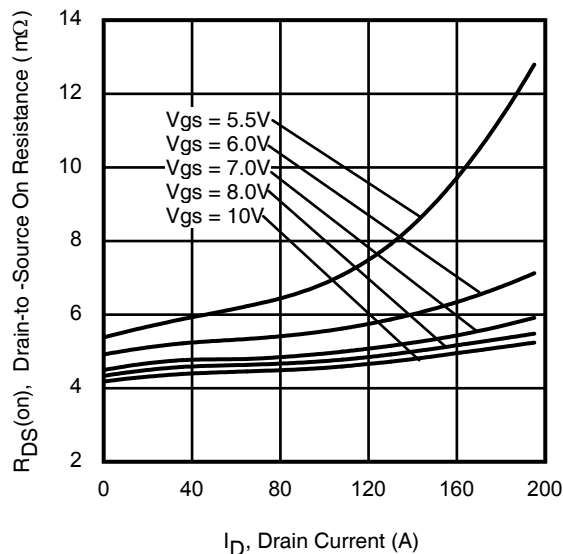
**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

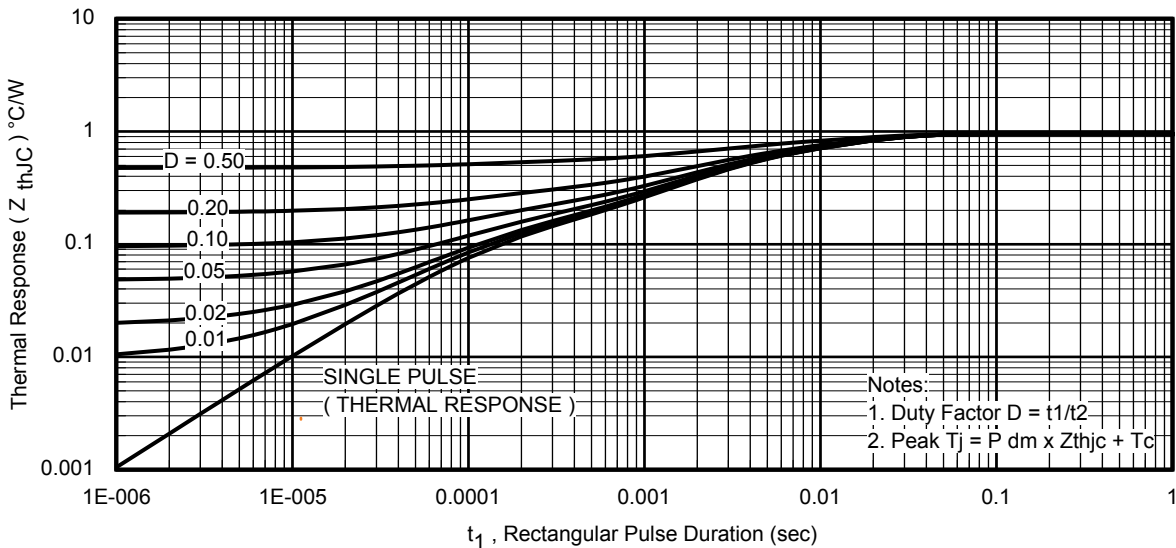
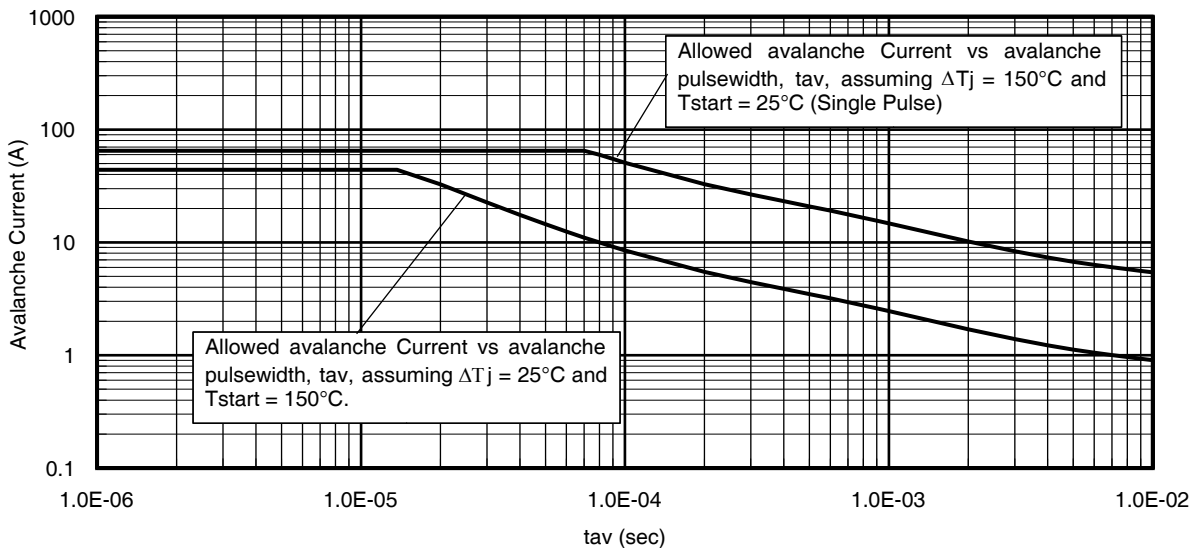
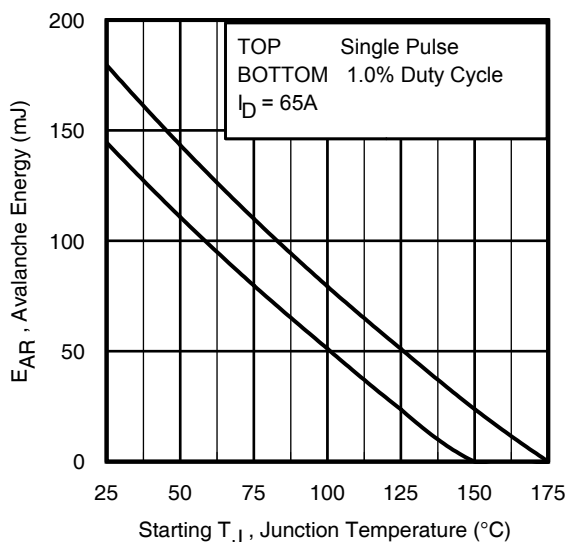
| Symbol                    | Parameter   | Min. | Typ. | Max. | Units | Conditions   |
|---------------------------|---|------|------|------|-------|--|
| g <sub>fs</sub>           | Forward Transconductance                                    | 110  | —    | —    | S     | V <sub>DS</sub> = 10V, I <sub>D</sub> = 65A  |
| Q <sub>g</sub>            | Total Gate Charge   | —    | 88   | 130  | nC    | I <sub>D</sub> = 65A<br>V <sub>DS</sub> = 30V<br>V <sub>GS</sub> = 10V   |
| Q <sub>gs</sub>           | Gate-to-Source Charge                                       | —    | 22   | —    |       |  |
| Q <sub>gd</sub>           | Gate-to-Drain Charge  | —    | 28   | —    |       |  |
| Q <sub>sync</sub>         | Total Gate Charge Sync. (Q <sub>g</sub> – Q <sub>gd</sub> ) | —    | 60   | —    |       |  |
| t <sub>d(on)</sub>        | Turn-On Delay Time  | —    | 12   | —    | ns    | V <sub>DD</sub> = 30V<br>I <sub>D</sub> = 65A<br>R <sub>G</sub> = 2.7Ω<br>V <sub>GS</sub> = 10V ④  |
| t <sub>r</sub>            | Rise Time   | —    | 76   | —    |       |  |
| t <sub>d(off)</sub>       | Turn-Off Delay Time   | —    | 58   | —    |       |  |
| t <sub>f</sub>            | Fall Time   | —    | 56   | —    |       |  |
| C <sub>iss</sub>          | Input Capacitance   | —    | 4555 | —    | pF    | V <sub>GS</sub> = 0V<br>V <sub>DS</sub> = 25V<br>f = 1.0MHz, See Fig.7<br>V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 48V⑥<br>V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 48V⑤ |
| C <sub>oss</sub>          | Output Capacitance  | —    | 415  | —    |       |  |
| C <sub>riss</sub>         | Reverse Transfer Capacitance                                | —    | 270  | —    |       |  |
| C <sub>oss eff.(ER)</sub> | Effective Output Capacitance (Energy Related)               | —    | 430  | —    |       |  |
| C <sub>oss eff.(TR)</sub> | Output Capacitance (Time Related)                           | —    | 550  | —    |       |  |

**Diode Characteristics**

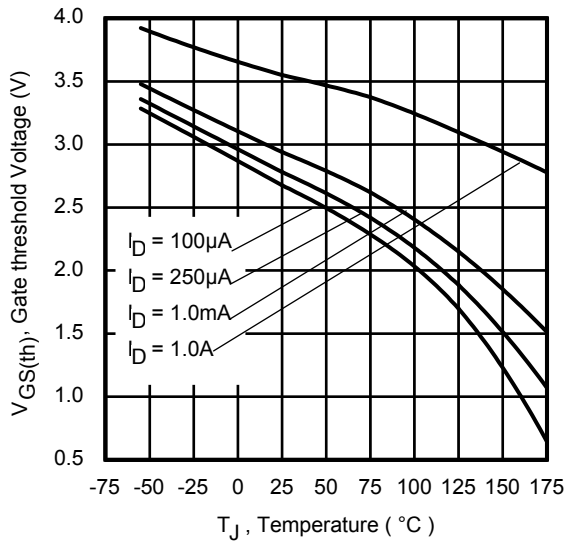
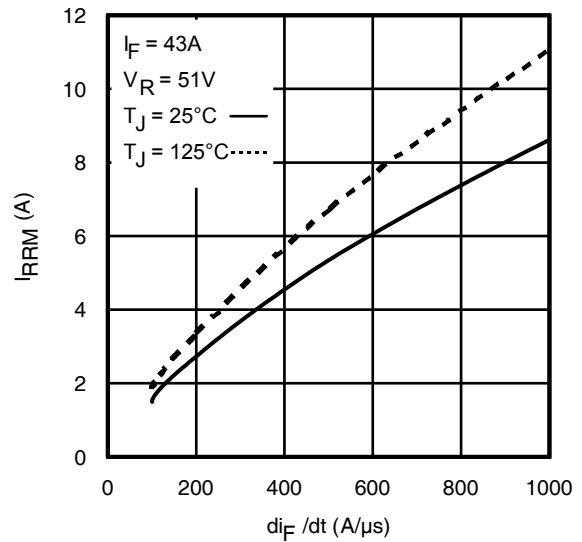
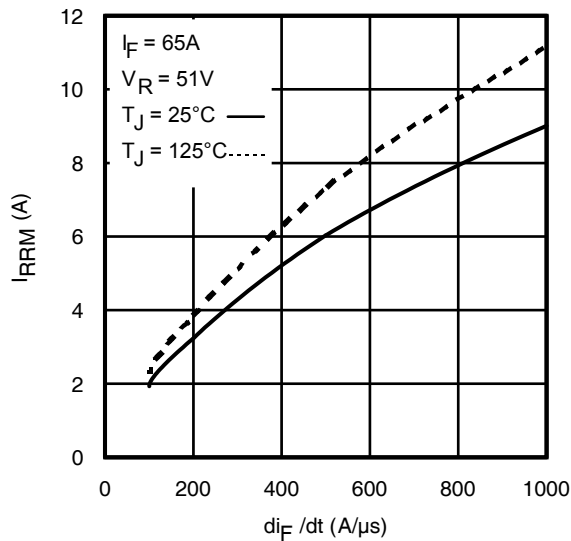
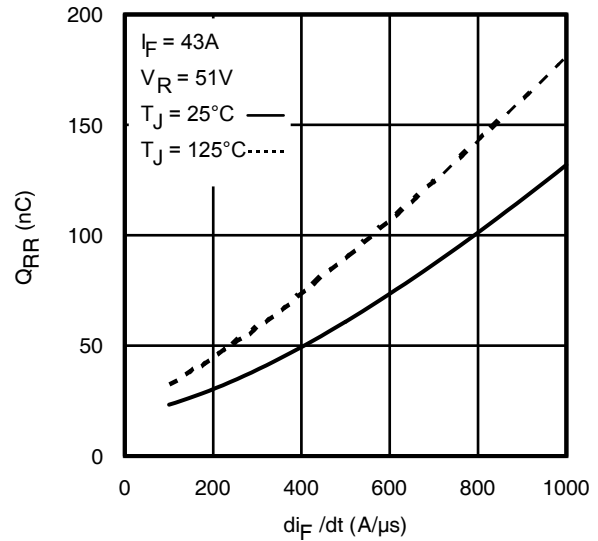
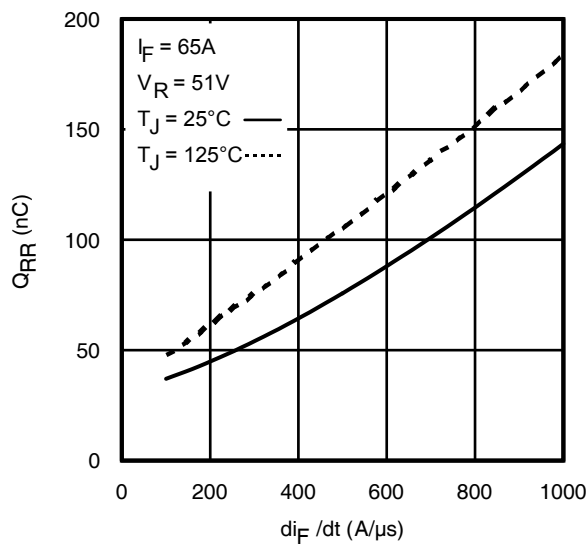
| Symbol           | Parameter                              | Min. | Typ. | Max. | Units | Conditions  |
|------------------|--|------|------|------|-------|---|
| I <sub>S</sub>   | Continuous Source Current (Body Diode) | —    | —    | 110  | A     | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I <sub>SM</sub>  | Pulsed Source Current (Body Diode) ①   | —    | —    | 430  |       |   |
| V <sub>SD</sub>  | Diode Forward Voltage                  | —    | —    | 1.2  | V     | T <sub>J</sub> = 25°C, I <sub>S</sub> = 65A, V <sub>GS</sub> = 0V ④   |
| dv/dt            | Peak Diode Recovery dv/dt              | —    | 11   | —    | V/ns  | T <sub>J</sub> = 175°C, I <sub>S</sub> = 65A, V <sub>DS</sub> = 60V③  |
| t <sub>rr</sub>  | Reverse Recovery Time                  | —    | 33   | —    | ns    | T <sub>J</sub> = 25°C V <sub>DD</sub> = 51V   |
|                  |  | —    | 37   | —    |       | T <sub>J</sub> = 125°C I <sub>F</sub> = 65A,  |
| Q <sub>rr</sub>  | Reverse Recovery Charge                | —    | 36   | —    | nC    | T <sub>J</sub> = 25°C di/dt = 100A/μs ④   |
|                  |  | —    | 47   | —    |       | T <sub>J</sub> = 125°C  |
| I <sub>RRM</sub> | Reverse Recovery Current               | —    | 1.9  | —    | A     | T <sub>J</sub> = 25°C   |

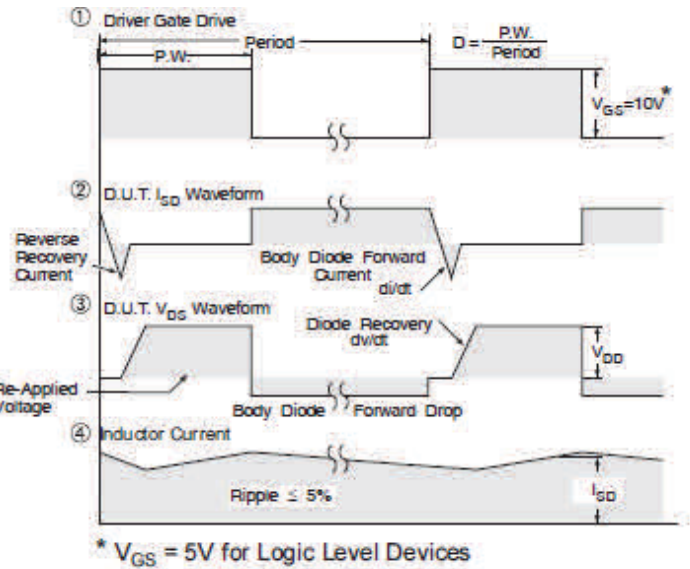
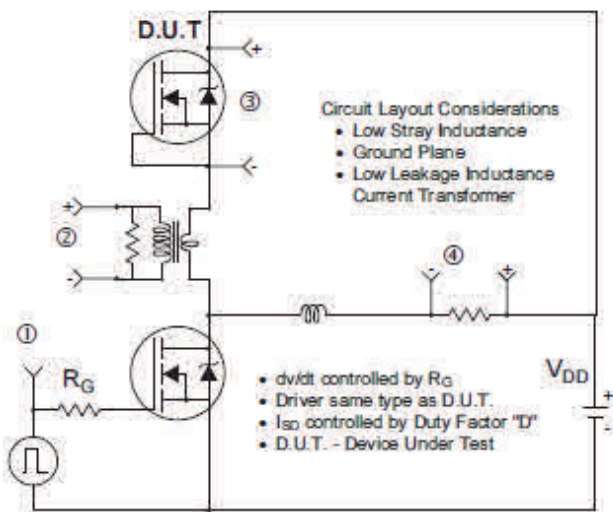
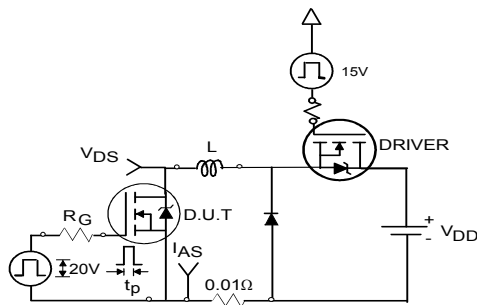
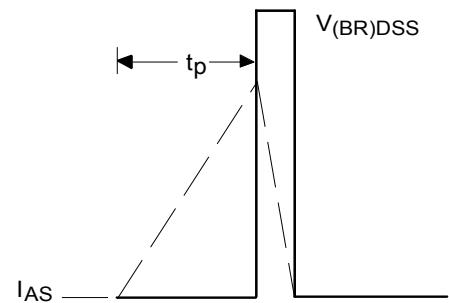
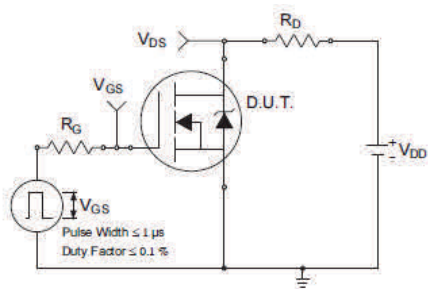
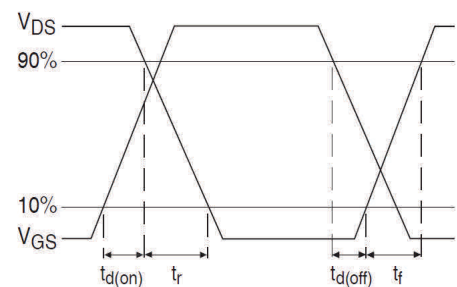

**Fig 3. Typical Output Characteristics**

**Fig 4. Typical Output Characteristics**

**Fig 5. Typical Transfer Characteristics**

**Fig 6. Normalized On-Resistance vs. Temperature**

**Fig 7. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 8. Typical Gate Charge vs. Gate-to-Source Voltage**

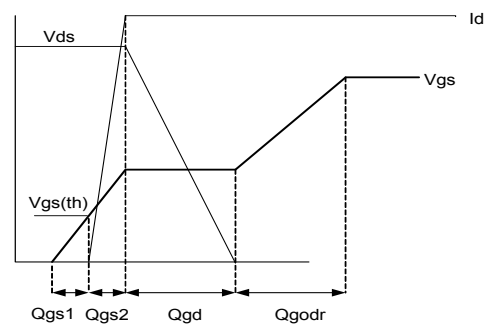

**Fig 9.** Typical Source-Drain Diode Forward Voltage

**Fig 10.** Maximum Safe Operating Area

**Fig 11.** Drain-to-Source Breakdown Voltage

**Fig 12.** Typical  $C_{oss}$  Stored Energy

**Fig 13.** Typical On-Resistance vs. Drain Current


**Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig 15. Avalanche Current vs. Pulse Width**

**Fig 16. Maximum Avalanche Energy vs. Temperature**
**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
**(For further info, see AN-1005 at www.irf.com)**

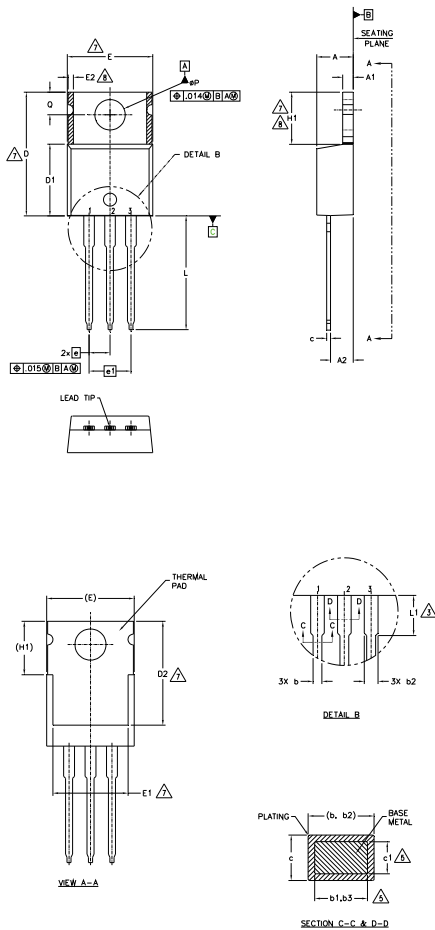
1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 14)  
 $P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$   
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$   
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$


**Fig 17. Threshold Voltage vs. Temperature**

**Fig 18. Typical Recovery Current vs. diF/dt**

**Fig 19. Typical Recovery Current vs. diF/dt**

**Fig 20. Typical Stored Charge vs. diF/dt**

**Fig 21. Typical Stored Charge vs. diF/dt**


**Fig 22. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**

**Fig 23a. Unclamped Inductive Test Circuit**

**Fig 23b. Unclamped Inductive Waveforms**

**Fig 24a. Switching Time Test Circuit**

**Fig 24b. Switching Time Waveforms**

**Fig 25a. Gate Charge Test Circuit**

**Fig 25b. Gate Charge Waveform**



**TO-220AB Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b2 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

| SYMBOL | DIMENSIONS  |       |          |      | NOTES |
|--------|-------------|-------|----------|------|-------|
|        | MILLIMETERS |       | INCHES   |      |       |
|        | MIN.        | MAX.  | MIN.     | MAX. |       |
| A      | 3.56        | 4.83  | .140     | .190 |       |
| A1     | 1.14        | 1.40  | .045     | .055 |       |
| A2     | 2.03        | 2.92  | .080     | .115 |       |
| b      | 0.38        | 1.01  | .015     | .040 |       |
| b1     | 0.38        | 0.97  | .015     | .038 | 5     |
| b2     | 1.14        | 1.78  | .045     | .070 |       |
| b3     | 1.14        | 1.73  | .045     | .068 | 5     |
| c      | 0.36        | 0.61  | .014     | .024 |       |
| c1     | 0.36        | 0.56  | .014     | .022 | 5     |
| D      | 14.22       | 16.51 | .560     | .650 | 4     |
| D1     | 8.38        | 9.02  | .330     | .355 |       |
| D2     | 11.68       | 12.88 | .460     | .507 | 7     |
| E      | 9.65        | 10.67 | .380     | .420 | 4,7   |
| E1     | 6.86        | 8.89  | .270     | .350 | 7     |
| E2     | -           | 0.76  | -        | .030 | 8     |
| e      | 2.54 BSC    |       | .100 BSC |      |       |
| e1     | 5.08 BSC    |       | .200 BSC |      |       |
| H1     | 5.84        | 6.86  | .230     | .270 | 7,8   |
| L      | 12.70       | 14.73 | .500     | .580 |       |
| L1     | 3.56        | 4.06  | .140     | .160 | 3     |
| ØP     | 3.54        | 4.08  | .139     | .161 |       |
| Q      | 2.54        | 3.42  | .100     | .135 |       |

**LEAD ASSIGNMENTS**
**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

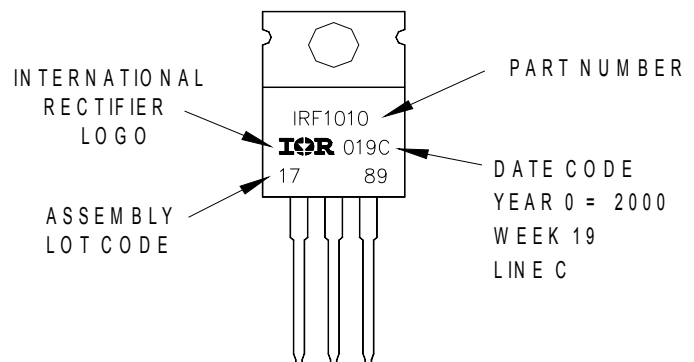
**DIODES**

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

**TO-220AB Part Marking Information**

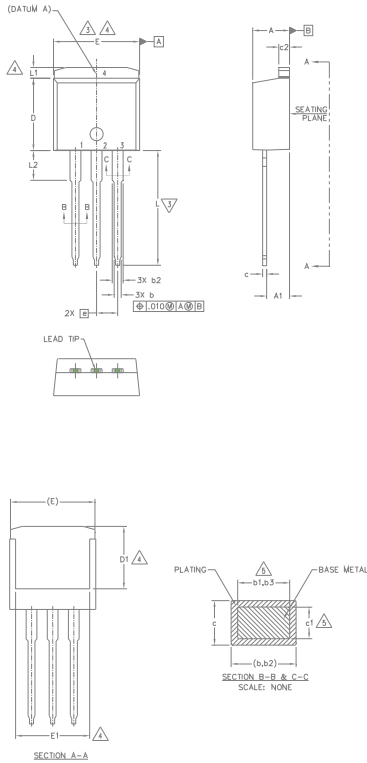
EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 2000  
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position  
 indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**TO-262 Package Outline (Dimensions are shown in millimeters (inches))**


| SYMBOL | DIMENSIONS  |       |          |      | NOTES |
|--------|-------------|-------|----------|------|-------|
|        | MILLIMETERS |       | INCHES   |      |       |
|        | MIN.        | MAX.  | MIN.     | MAX. |       |
| A      | 4.06        | 4.83  | .160     | .190 | 5     |
| A1     | 2.03        | 3.02  | .080     | .119 |       |
| b      | 0.51        | 0.99  | .020     | .039 |       |
| b1     | 0.51        | 0.89  | .020     | .035 |       |
| b2     | 1.14        | 1.78  | .045     | .070 |       |
| b3     | 1.14        | 1.73  | .045     | .068 |       |
| c      | 0.38        | 0.74  | .015     | .029 |       |
| c1     | 0.38        | 0.58  | .015     | .023 |       |
| c2     | 1.14        | 1.65  | .045     | .065 |       |
| D      | 8.38        | 9.65  | .330     | .380 |       |
| D1     | 6.86        | -     | .270     | -    | 4     |
| E      | 9.65        | 10.67 | .380     | .420 | 3,4   |
| E1     | 6.22        | -     | .245     | -    | 4     |
| e      | 2.54 BSC    |       | .100 BSC |      |       |
| L      | 13.46       | 14.10 | .530     | .555 | 4     |
| L1     | -           | 1.65  | -        | .065 |       |
| L2     | 3.56        | 3.71  | .140     | .146 |       |

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

**LEAD ASSIGNMENTS**
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

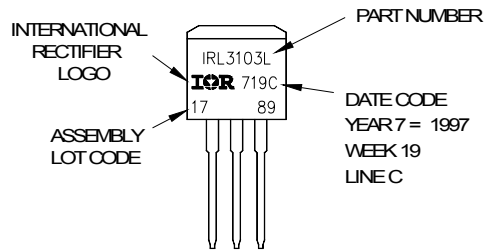
**DIODES**

- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2, 4.- CATHODE
- 3.- ANODE

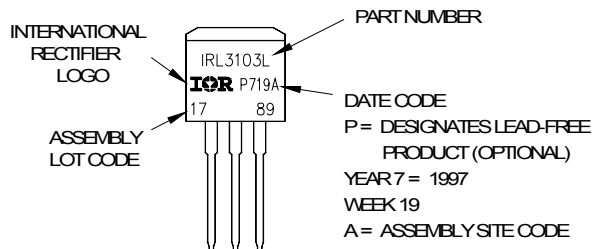
**TO-262 Part Marking Information**

EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON VWV19, 1997  
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"

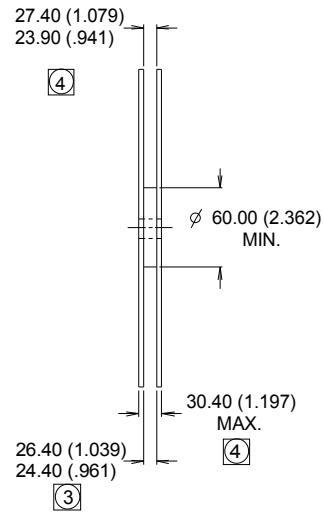
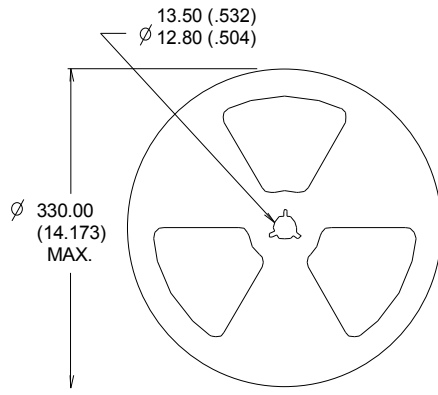
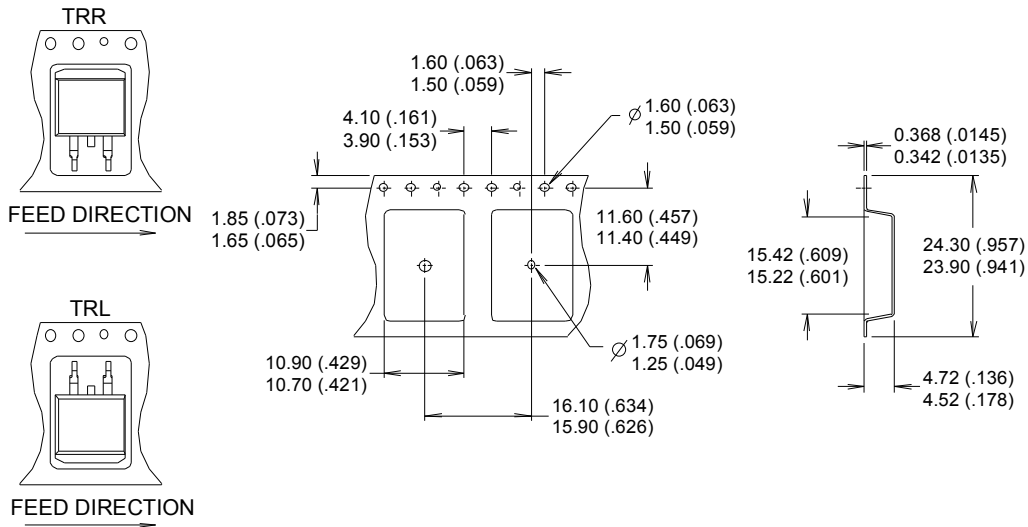


OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



**D<sup>2</sup>Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))**

**NOTES :**

1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification Information<sup>†</sup>**

|                                   |   |      |
|-----------------------------------|---|------|
| <b>Qualification Level</b>        | Industrial<br>(per JEDEC JESD47F) <sup>††</sup> |      |
| <b>Moisture Sensitivity Level</b> | TO-220  | N/A  |
|                                   | D <sup>2</sup> Pak                              | MSL1 |
|                                   | TO-262  | N/A  |
| <b>RoHS Compliant</b>             | Yes   |      |

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

**Revision History**

| <b>Date</b> | <b>Comments</b>  |
|-------------|--|
| 11/6/2014   | <ul style="list-style-type: none"> <li>Updated <math>E_{AS(L=1mH)} = 313mJ</math> on page 2</li> <li>Updated note 8 "Limited by <math>T_{Jmax}</math>, starting <math>T_J = 25^{\circ}C</math>, <math>L = 1mH</math>, <math>R_G = 50\Omega</math>, <math>I_{AS} = 25A</math>, <math>V_{GS} = 10V</math>". on page 2</li> <li>Updated package outline on page 9,10,11.</li> </ul> |

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[SSM6P69NU,LF](#) [DMP22D4UFO-7B](#)